

ABSTRACT OF THE DISCLOSURE

A method for obtaining a P type GaN compound semiconductor in a GaN compound semiconductor element. An N type GaN compound semiconductor layer is formed on a substrate. A GaN compound semiconductor layer to which a P type impurity is doped is formed on the N type GaN compound semiconductor layer. The GaN compound semiconductor layer to which the P type impurity is doped is irradiated with electromagnetic radiation of a predetermined wavelength to selectively agitate hydrogen bonds to dissociate H, and activate P type impurity as an acceptor.

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